

ABSTRACT

A minute semiconductor device having a high driving ability and a manufacturing method thereof are provided. A semiconductor device includes a support substrate, an insulating layer that is formed above the support substrate, a semiconductor layer that is formed above the insulating layer, a channel region that is provided in the semiconductor layer, a source region and a drain region that are formed so as to sandwich the channel region, and a gate electrode that is formed above the channel region via a gate insulating layer. The boundary between the gate insulating layer and the channel region has a wave-like pattern of a gradual slope without any corners.